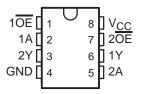
SCES208F - APRIL 1999 - REVISED SEPTEMBER 2003

- **Available in the Texas Instruments** NanoStar™ and NanoFree™ Packages
- Supports 5-V V<sub>CC</sub> Operation
- Inputs Accept Voltages to 5.5 V
- Max tpd of 4.6 ns at 3.3 V
- Low Power Consumption, 10-µA Max I<sub>CC</sub>
- ±24-mA Output Drive at 3.3 V
- Typical V<sub>OI P</sub> (Output Ground Bounce) <0.8 V at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$
- Typical V<sub>OHV</sub> (Output V<sub>OH</sub> Undershoot) >2 V at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C
- **Ioff Supports Partial-Power-Down Mode** Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- **ESD Protection Exceeds JESD 22** 
  - 2000-V Human-Body Model (A114-A)
  - 1000-V Charged-Device Model (C101)

#### **DCT OR DCU PACKAGE** (TOP VIEW)



#### YEA, YEP, YZA, OR YZP PACKAGE (BOTTOM VIEW)

GND	04	50	2A
2Y	03	60	1Y
1A 1OE	02	70	2OE
10E	O 1	80	Vcc

#### description/ordering information

This dual buffer/driver is designed for 1.65-V to 5.5-V V<sub>CC</sub> operation.

The SN74LVC2G240 is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

#### ORDERING INFORMATION

TA	PACKAGE <sup>†</sup>	ORDERABLE PART NUMBER	TOP-SIDE MARKING‡		
	NanoStar™ – WCSP (DSBGA) 0.17-mm Small Bump – YEA		SN74LVC2G240YEAR		
–40°C to 85°C	NanoFree™ – WCSP (DSBGA) 0.17-mm Small Bump – YZA (Pb-free)	Tape and reel	SN74LVC2G240YZAR	014	
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP		SN74LVC2G240YEPR	CK_	
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)		SN74LVC2G240YZPR		
	SSOP - DCT	Tape and reel	SN74LVC2G240DCTR	C40	
	VSSOP - DCU	Tape and reel	SN74LVC2G240DCUR	C40_	

<sup>†</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site. DCU: The actual top-side marking has one additional character that designates the assembly/test site. YEA/YZA, YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition  $(1 = SnPb, \bullet = Pb-free).$ 



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NanoStar and NanoFree are trademarks of Texas Instruments.



#### description/ordering information (continued)

This device is organized as two 1-bit buffers/drivers with separate output-enable ( $\overline{OE}$ ) inputs. When  $\overline{OE}$  is low, the device passes data from the A input to the Y output. When  $\overline{OE}$  is high, the outputs are in the high-impedance state.

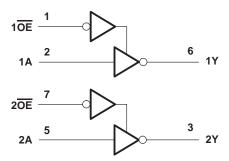
To ensure the high-impedance state during power up or power down,  $\overline{\text{OE}}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for partial-power-down applications using I<sub>off</sub>. The I<sub>off</sub> circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

FUNCTION TABLE (each buffer)

INP	JTS	OUTPUT
OE	Α	Υ
L	Н	L
L	L	Н
Н	Χ	Z

#### logic diagram (positive logic)





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### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub>	
Voltage range applied to any output in the high-impedance or power-off state, V <sub>O</sub> (see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, VO	
(see Notes 1 and 2)	$\dots$ -0.5 V to V <sub>CC</sub> + 0.5 V
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	
Continuous output current, I <sub>O</sub>	
Continuous current through V <sub>CC</sub> or GND	
Package thermal impedance, θ <sub>JA</sub> (see Note 3): DCT package	
DCU package	
YEA/YZA package	
YEP/YZP package	
Storage temperature range, T <sub>stg</sub>	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. The value of  $V_{\hbox{\footnotesize{CC}}}$  is provided in the recommended operating conditions table.
- 3. The package thermal impedance is calculated in accordance with JESD 51-7.



### recommended operating conditions (see Note 4)

			MIN	MAX	UNIT			
\ /	Our miles and the me	Operating	1.65	5.5				
VCC	Supply voltage	Data retention only	1.5		V			
		V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>					
.,	18.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		.,			
$V_{IH}$	High-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V	2		V			
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$0.7 \times V_{CC}$					
		V <sub>CC</sub> = 1.65 V to 1.95 V		0.35 × V <sub>CC</sub>				
\ /	Lava lava Paradovalia na	V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	.,			
$V_{IL}$	Low-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V		0.8	V			
		V <sub>CC</sub> = 4.5 V to 5.5 V		$0.3 \times V_{CC}$				
VI	Input voltage		0	5.5	V			
.,	Output and to me	High or low state	0	Vcc	V			
VO	Output voltage	3-state	0	5.5	V			
		V <sub>CC</sub> = 1.65 V		-4				
		V <sub>CC</sub> = 2.3 V		-8				
loh	High-level output current			-16	mA			
		VCC = 3 V		-24				
		V <sub>CC</sub> = 4.5 V		-32				
		V <sub>CC</sub> = 1.65 V		4				
		V <sub>CC</sub> = 2.3 V		8				
loL	Low-level output current			16	mA			
		VCC = 3 V		24				
		V <sub>CC</sub> = 4.5 V		32				
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20				
Δt/Δν	Input transition rise or fall rate	V <sub>CC</sub> = 3.3 V ± 0.3 V						
		V <sub>CC</sub> = 5 V ± 0.5 V		5	1			
TA	Operating free-air temperature		-40	85	°C			

NOTE 4: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



#### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	VCC	MIN	TYP†	MAX	UNIT
	$I_{OH} = -100 \mu\text{A}$	1.65 V to 5.5 V	V <sub>CC</sub> -0.1			
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2			
	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9			
VOH	I <sub>OH</sub> = -16 mA		2.4			V
	I <sub>OH</sub> = -24 mA	3 V	2.3			
	I <sub>OH</sub> = -32 mA	4.5 V	3.8			
	I <sub>OL</sub> = 100 μA	1.65 V to 5.5 V			0.1	
	I <sub>OL</sub> = 4 mA	1.65 V			0.45	
	I <sub>OL</sub> = 8 mA	2.3 V			0.3	
VOL	I <sub>OL</sub> = 16 mA				0.4	V
	I <sub>OL</sub> = 24 mA	3 V			0.55	
	I <sub>OL</sub> = 32 mA	4.5 V			0.55	
I <sub>I</sub> A or OE inputs	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			±5	μΑ
loff	$V_I$ or $V_O = 5.5 V$	0			±10	μΑ
loz	V <sub>O</sub> = 0 to 5.5 V	3.6 V			10	μΑ
Icc	$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V			10	μΑ
ΔlCC	One input at V <sub>CC</sub> – 0.6 V, Other inputs at V <sub>CC</sub> or GND	3 V to 5.5 V			500	μΑ
C <sub>i</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V		4		pF
Co	$V_O = V_{CC}$ or GND	3.3 V		6		pF

 $<sup>^{\</sup>dagger}$  All typical values are at VCC = 3.3 V, TA = 25°C.

# switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

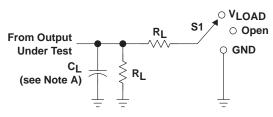
	PARAMETER FROM		PARAMETER FROM TO (INPUT) (OUTPUT)			= 1.8 V V <sub>CC</sub> = 2.5 V .15 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 5 V ± 0.5 V		UNIT
		(INPUT)	(001P01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	<sup>t</sup> pd	Α	Υ	2	11.3	1.4	5.5	1.1	4.6	1	4	ns
	t <sub>en</sub>	ŌE	Υ	2.7	11.7	1.9	6.6	1.4	5.4	1.1	5	ns
	<sup>t</sup> dis	ŌĒ	Υ	1.7	12.8	0.8	5.7	1.2	5.5	0.5	4.2	ns

### operating characteristics, $T_A = 25^{\circ}C$

	PARAMETER		TEST CONDITIONS	V <sub>CC</sub> = 1.8 V TYP	V <sub>CC</sub> = 2.5 V TYP	V <sub>CC</sub> = 3.3 V TYP	V <sub>CC</sub> = 5 V TYP	UNIT
<u> </u>	Power dissipation	Outputs enabled	( 40 MH-			15	17	~F
C <sub>pd</sub>	capacitance per buffer/driver	Outputs disabled	f = 10 MHz	1	1	2	3	pF



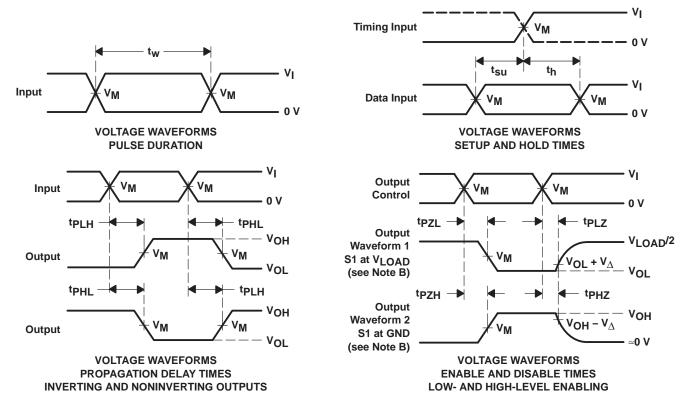
#### PARAMETER MEASUREMENT INFORMATION



TEST	S1
tPLH/tPHL	Open
tPLZ/tPZL	VLOAD
tPHZ/tPZH	GND

**LOAD CIRCUIT** 

.,	INPUTS		.,	V	•	D.	.,
VCC	٧ <sub>I</sub>	t <sub>r</sub> /t <sub>f</sub>	VM	VLOAD	CL	RL	$v_{\!\scriptscriptstyle\Delta}$
1.8 V $\pm$ 0.15 V	VCC	≤ <b>2</b> ns	V <sub>CC</sub> /2	2×V <sub>CC</sub>	30 pF	<b>1 k</b> Ω	0.15 V
2.5 V $\pm$ 0.2 V	VCC	≤ <b>2</b> ns	V <sub>CC</sub> /2	2×VCC	30 pF	<b>500</b> Ω	0.15 V
3.3 V $\pm$ 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	<b>500</b> Ω	0.3 V
5 V $\pm$ 0.5 V	VCC	≤2.5 ns	V <sub>CC</sub> /2	2×V <sub>CC</sub>	50 pF	<b>500</b> Ω	0.3 V



- NOTES: A. C<sub>I</sub> includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z<sub>Ω</sub> = 50 Ω.
  - D. The outputs are measured one at a time with one transition per measurement.
  - E. tpLZ and tpHZ are the same as tdis.
  - F. tpzL and tpzH are the same as ten.
  - G. tpLH and tpHL are the same as tpd.
  - H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms



#### DCT (R-PDSO-G8)

#### PLASTIC SMALL-OUTLINE PACKAGE

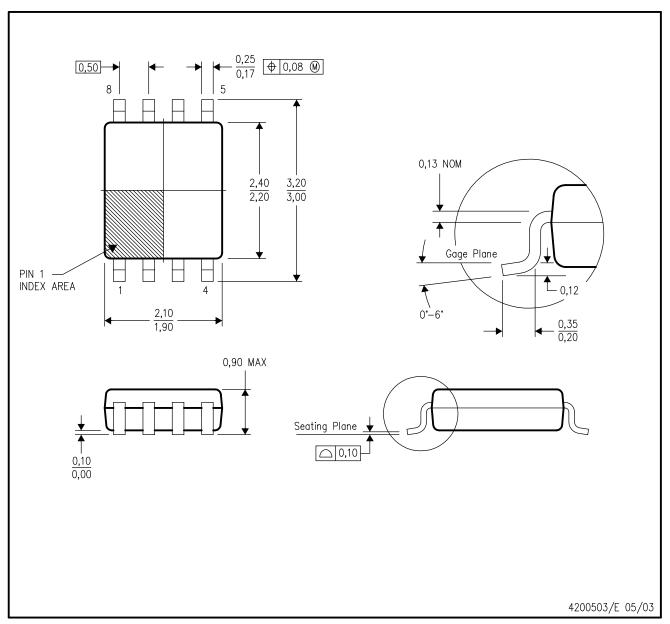


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. Falls within JEDEC MO-187 variation DA.

## DCU (R-PDSO-G8)

## PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



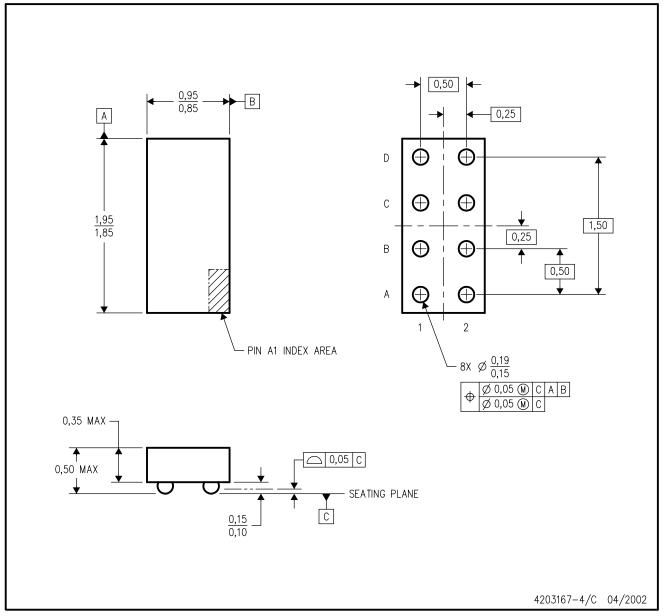
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation CA.



## YEA (R-XBGA-N8)

### DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

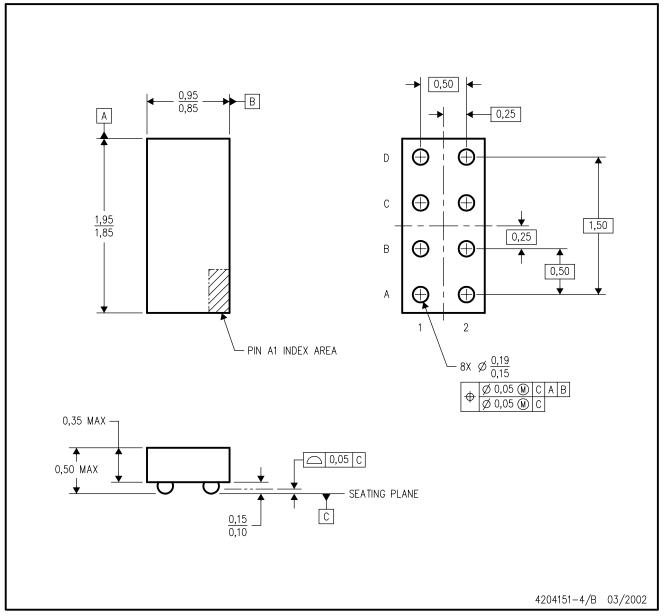
- B. This drawing is subject to change without notice.
- C. NanoStar  $\mathbf{M}$  package configuration.
- D. Package complies to JEDEC MO-211 variation EB.
- E. This package is tin-lead (SnPb). Refer to the 8 YZA package (drawing 4204151) for lead-free.

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## YZA (R-XBGA-N8)

### DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

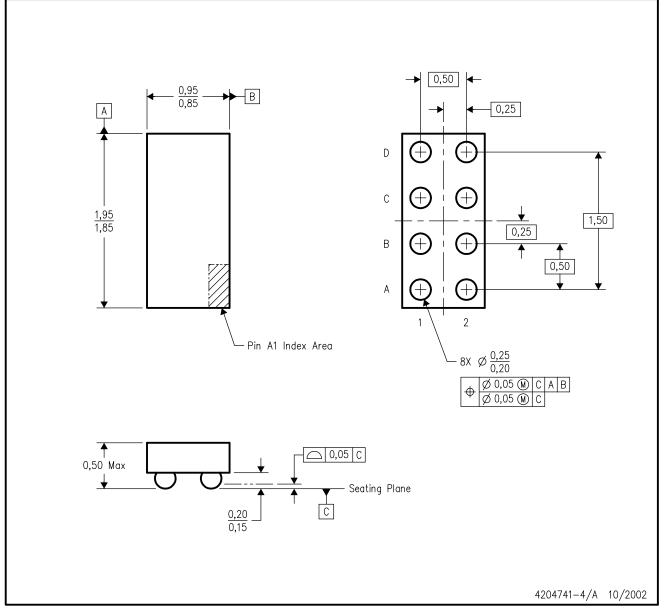
- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. Package complies to JEDEC MO-211 variation EB.
- E. This package is lead-free. Refer to the 8 YEA package (drawing 4203167) for tin-lead (SnPb).

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## YZP (R-XBGA-N8)

### DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

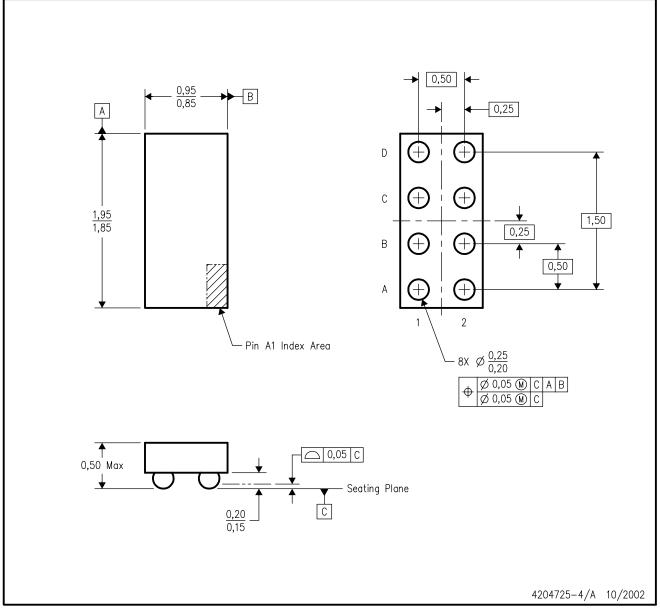
- B. This drawing is subject to change without notice.
- C. NanoFree  $^{\text{TM}}$  package configuration.
- D. This package is lead-free. Refer to the 8 YEP package (drawing 4204725) for tin-lead (SnPb).

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## YEP (R-XBGA-N8)

### DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar  $\mathbf{M}$  package configuration.
- D. This package is tin-lead (SnPb). Refer to the 8 YZP package (drawing 4204741) for lead-free.

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